

Power MOSFET

NTGD3148N

20 V, 3.5 A, Dual N-Channel, TSOP-6

Features

- Low Threshold Levels, $V_{GS(th)} < 1.5\text{ V}$
- Low Gate Charge (3.8 nC)
- Leading Edge Trench Technology of Low $R_{DS(on)}$
- High Power and Current Handling Capability
- This is a Pb-Free Device

Applications

- DC-DC Converters (Buck and Boost Circuits)
- Low Side Load Switch
- Optimized for Battery and Load Management Applications in Portable Equipment Like Cell Phones, DSCs, Media Player, Etc
- Battery Charging and Protection Circuits

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	3.0	A
		$T_A = 85^\circ\text{C}$		2.2	
Continuous Drain Current (Note 1)	$t \leq 5\text{ s}$	$T_A = 25^\circ\text{C}$	I_D	3.5	A
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	0.9	W
	$t \leq 5\text{ s}$			1.1	
Pulsed Drain Current		$t_p = 10\ \mu\text{s}$	I_{DM}	10	A
Operating Junction and Storage Temperature			T_J, T_{STG}	-50 to 150	$^\circ\text{C}$
Source Current (Body Diode)			I_S	0.8	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

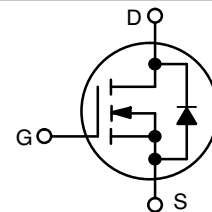
Parameter	Symbol	Value	Unit
Junction-to-Ambient — Steady State (Note 1)	$R_{\theta JA}$	140	$^\circ\text{C/W}$
Junction-to-Ambient — $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	110	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

N-CHANNEL MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
20 V	70 m Ω @ 4.5 V	3.5 A
	100 m Ω @ 2.5 V	

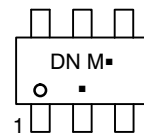


N-CHANNEL MOSFET



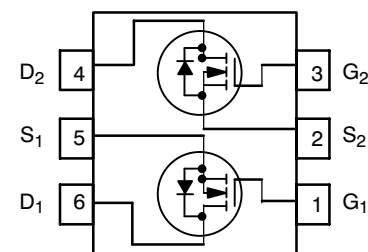
TSOP-6
CASE 318G
STYLE 13

MARKING DIAGRAM



DN = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PIN CONNECTION



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NTGD3148N

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 250 μA, Ref to 25°C		12.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C		1.0	μA
			T _J = 125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.5		1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			3.28		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.5 A		41.7	70	mΩ
		V _{GS} = 2.5 V, I _D = 2.8 A		58	100	
Forward Transconductance	g _{FS}	V _{DS} = 5.0 V, I _D = 3.5 A		6.2		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V		300		pF
Output Capacitance	C _{OSS}			73		
Reverse Transfer Capacitance	C _{RSS}			44		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 3.5 A		3.8		nC
Threshold Gate Charge	Q _{G(TH)}			0.3		
Gate-to-Source Charge	Q _{GS}			0.7		
Gate-to-Drain Charge	Q _{GD}			1.1		
Gate Resistance	R _G			2.8		Ω

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 3.5 A, R _G = 3.0 Ω		7.4		ns
Rise Time	t _r			11.2		
Turn-Off Delay Time	t _{d(OFF)}			12.8		
Fall Time	t _f			1.6		

DRAIN-TO-SOURCE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _D = 0.8 A	T _J = 25°C		0.71	V
			T _J = 125°C		0.57	
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, d _{IS} /d _t = 100 A/μs, I _S = 0.8 A		9.0		ns
Charge Time	T _a			5.0		
Discharge Time	T _b			4.0		
Reverse Recovery Time	Q _{RR}			2.5		

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTGD3148NT1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.